



175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D Τ _C = +25°C
-40V	$11m\Omega @ V_{GS} = -10V$	-45A
	15mΩ @ $V_{GS} = -4.5V$	-40A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

Features and Benefits

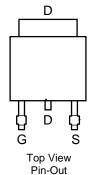
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

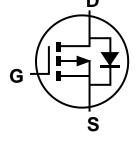
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.33 grams (Approximate)



Top View





Equivalent Circuit

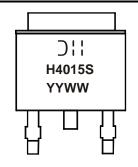
Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH4015SK3-13	TO252	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



DII = Manufacturer's Marking H4015S = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 15 = 2015) WW = Week (01 - 53)



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	-40	V		
Gate-Source Voltage	V _{GSS}	±25	V		
Continuous Dusin Comment (Nata C) // 40 //	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	-45 -35	А
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I _D	-14 -10	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-100	Α		
Maximum Body Diode Forward Current (Note 6)	I _S	-5.5	A		
Avalanche Current, L = 1mH (Note 7)	I _{AS}	-22	Α		
Avalanche Energy, L = 1mH (Note 7)	E _{AS}	260	mJ		

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)		P_D	1.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	73	°C/W
Total Power Dissipation (Note 6)		P_D	3.3	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{ heta JA}$	38	°C/W
Thermal Resistance, Junction to Case		$R_{ heta JC}$	1.0	C/VV
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +175	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)				•			
Drain-Source Breakdown Voltage	BV _{DSS}	-40	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	-1.5	-2	-2.5	٧	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance			8	11	0	$V_{GS} = -10V, I_{D} = -9.8A$	
Static Diain-Source On-Resistance	R _{DS(ON)}	_	11	15	mΩ	$V_{GS} = -4.5V, I_{D} = -9.8A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}		4234	_		$V_{DS} = -20V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		1036	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	526	_			
Gate Resistance	R_g	_	7.8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	42.7	_		V _{DS} = -20V,	
Total Gate Charge (V _{GS} = -10V)	Q_g	_	91	_	nC		
Gate-Source Charge	Qgs	_	14.2	_	IIC	$I_D = -9.8A$	
Gate-Drain Charge	Q_{gd}	_	13.5	_			
Turn-On Delay Time	t _{D(ON)}	_	13.2	_		$V_{GS} = -10V, V_{DD} = -20V,$ $R_{G} = 6\Omega, I_{D} = -1A$	
Turn-On Rise Time	t _R	_	10	_			
Turn-Off Delay Time	t _{D(OFF)}	_	303	_	ns		
Turn-Off Fall Time	t _F	_	138	_			
Reverse Recovery Time	t _{RR}	_	26	_	ns	I _F = -9.8A, di/dt = -100A/µs	
Reverse Recovery Charge	Q_{RR}	_	20	_	nC	I _F = -9.8A, di/dt = -100A/µs	

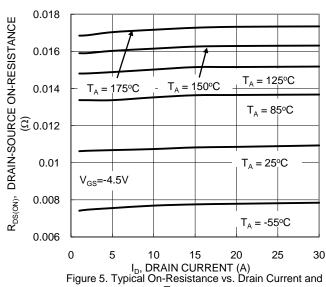
Iotes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.

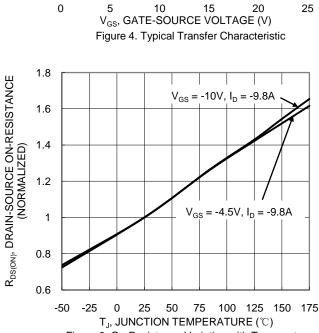
8. Short duration pulse test used to minimize self-heating effect.

Guaranteed by design. Not subject to product testing.

30.0 20 V_{DS}= -5.0V $V_{GS} = -10.0V$ 25.0 16 '_{GS} = -5.0V ID, DRAIN CURRENT (A) ID, DRAIN CURRENT (A) 20.0 12 $V_{GS} = -3.0V$ -3.5V 15.0 8 10.0 T_A = 175°C 4 $T_A = 150^{\circ}C$ 5.0 $V_{GS} = -2.5V$ $T_A = 125^{\circ}C$ 0.0 0 0 0.4 8.0 1.2 1.6 2 1 1.5 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic Figure 2. Typical Transfer Characteristic 0.03 0.014 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.025 0.012 $V_{GS} = -4.5V$ 0.02 0.010 0.015 0.008 $V_{GS} = -10.0V$ 0.01 0.006 0.005 0.004 0 0 5 10 15 20 25 30 0 10 I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage 0.018 1.8 0.016 1.6



Temperature



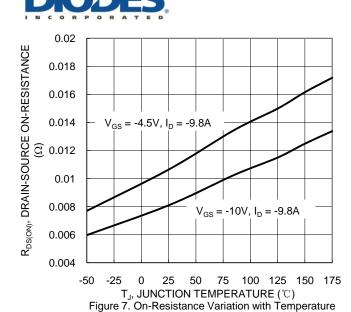
DMPH4015SK3

 $T_A = 8.5^{\circ}C$

= 25°C

= -55°C

 $I_{D} = -9.8A$



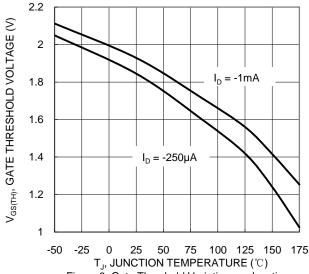
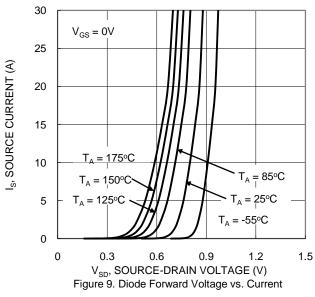
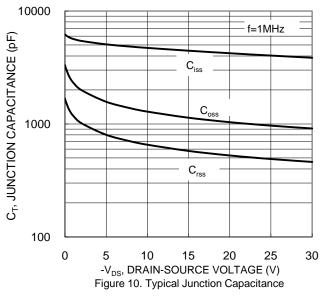
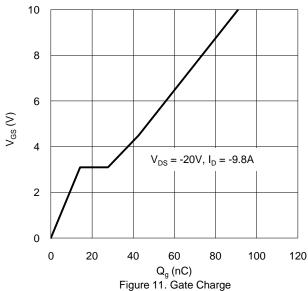
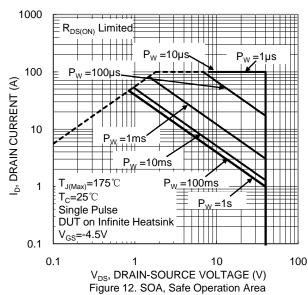


Figure 8. Gate Threshold Variation vs. Junction Temperature











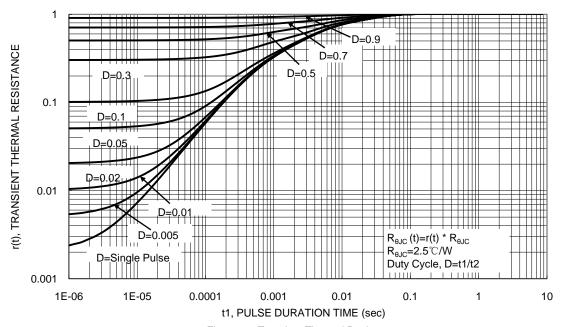


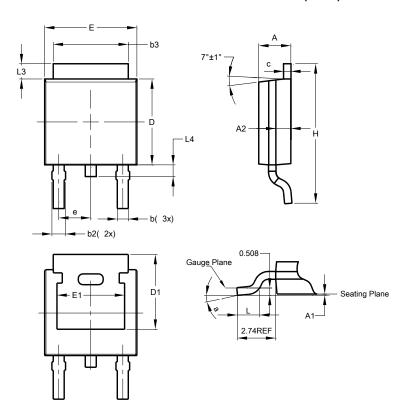
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

TO252 (DPAK)

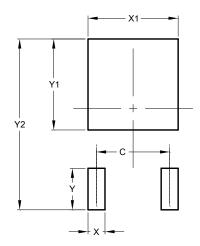


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)			
C	4.572			
Х	1.060			
X1	5.632			
Y	2.600			
Y1	5.700			
Y2	10.700			



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